

General Purpose Transistor

PNP Silicon

NST3906MX2

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

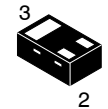
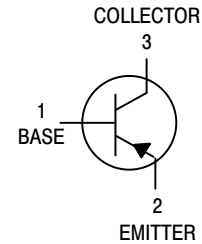
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	–40	Vdc
Collector – Base Voltage	V_{CBO}	–40	Vdc
Emitter – Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous (Note 1)	I_C	–200	mA _{dc}
Collector Current – Peak (Note 1)	I_{CM}	–800	mA _{dc}

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

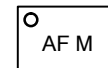
Characteristic	Symbol	Max	Unit
Total Power Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	165 1.39	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	720	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	590 4.93	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	203	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

- Reference SOA Curve
- Surface-mounted on FR4 board using a 0.6 mm^2 , 2 oz. Cu pad
- Surface-mounted on FR4 board using a 100 mm^2 , 2 oz. Cu pad



X2DFN3 (1.0 x 0.6 mm)
CASE 714AC

MARKING DIAGRAM



AF = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3906MX2T5G	X2DFN3 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST3906MX2

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = –1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	–40	–	V _{dc}
Collector – Base Breakdown Voltage (I _C = –10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	–40	–	V _{dc}
Emitter – Base Breakdown Voltage (I _E = –10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	–5.0	–	V _{dc}
Base Cutoff Current (V _{CE} = –30 V _{dc} , V _{EB} = –3.0 V _{dc})	I _{BL}	–	–50	nA _{dc}
Collector Cutoff Current (V _{CE} = –30 V _{dc} , V _{EB} = –3.0 V _{dc})	I _{CEX}	–	–50	nA _{dc}

ON CHARACTERISTICS (Note 4)

DC Current Gain (I _C = –0.1 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –1.0 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –10 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –50 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –100 mA _{dc} , V _{CE} = –1.0 V _{dc})	H _{FE}	60 80 100 60 30	– – 300 – –	–
Collector – Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{CE(sat)}	– –	–0.25 –0.4	V _{dc}
Base – Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{BE(sat)}	–0.65 –	–0.85 –0.95	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I _C = –10 mA _{dc} , V _{CE} = –20 V _{dc} , f = 100 MHz)	f _T	250	–	MHz
Output Capacitance (V _{CB} = –5.0 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	4.5	pF
Input Capacitance (V _{EB} = –0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	–	10	pF
Input Impedance (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{re}	0.1	10	X 10 ^{–4}
Small – Signal Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{fe}	100	400	–
Output Admittance (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure (I _C = –100 μA _{dc} , V _{CE} = –5.0 V _{dc} , R _S = 1.0 kΩ, f = 1.0 kHz)	NF	–	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = –3.0 V _{dc} , V _{BE} = 0.5 V _{dc} , I _C = –10 mA _{dc} , I _{B1} = –1.0 mA _{dc})	t _d	–	35	ns
Rise Time		t _r	–	35	
Storage Time	(V _{CC} = –3.0 V _{dc} , I _C = –10 mA _{dc} , I _{B1} = I _{B2} = –1.0 mA _{dc})	t _s	–	225	ns
Fall Time		t _f	–	75	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

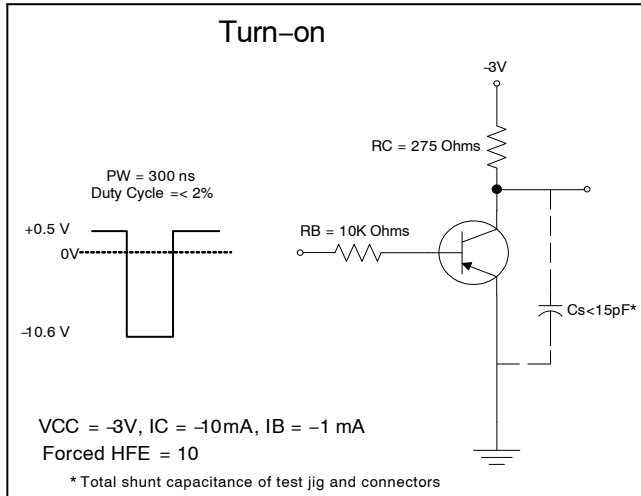


Figure 1. Delay and Rise Time Equivalent Test Circuit

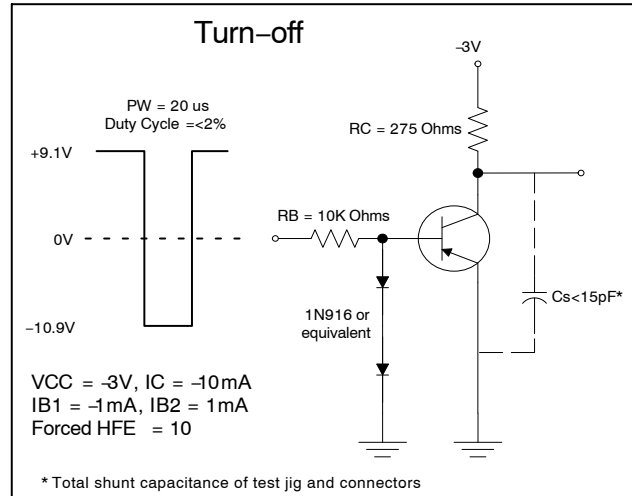


Figure 2. Storage and Fall Time Equivalent Test Circuit

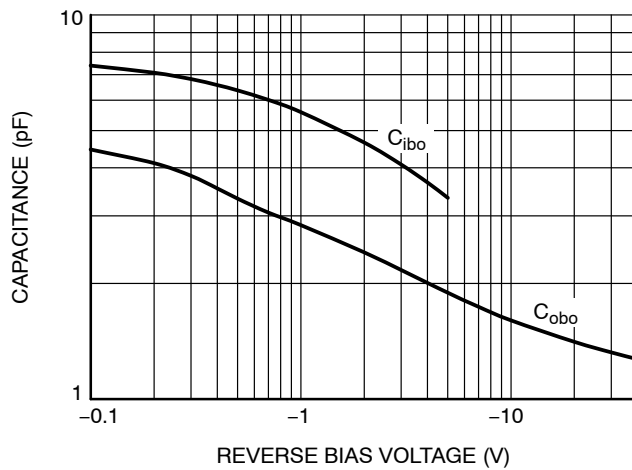


Figure 3. Capacitance

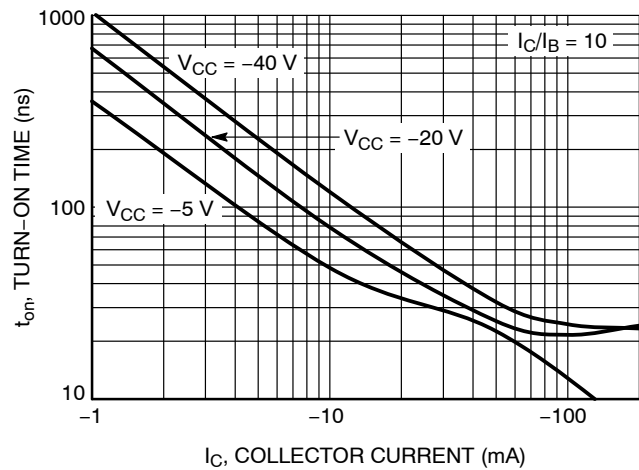


Figure 4. Turn-On Time

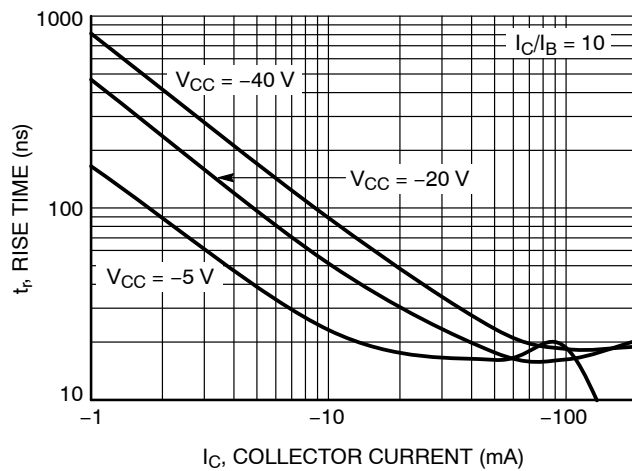


Figure 5. Rise Time

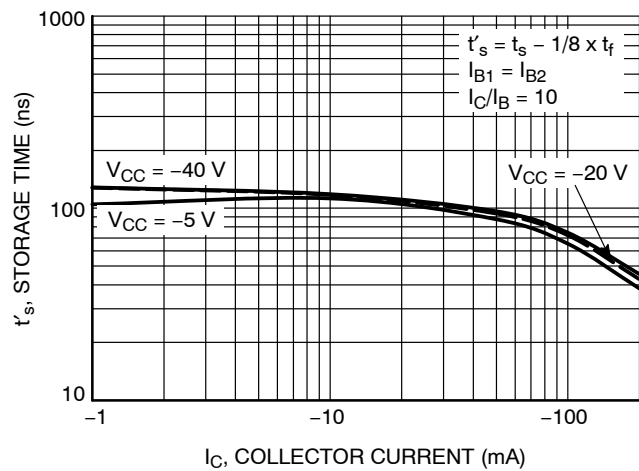


Figure 6. Storage Time

TYPICAL CHARACTERISTICS

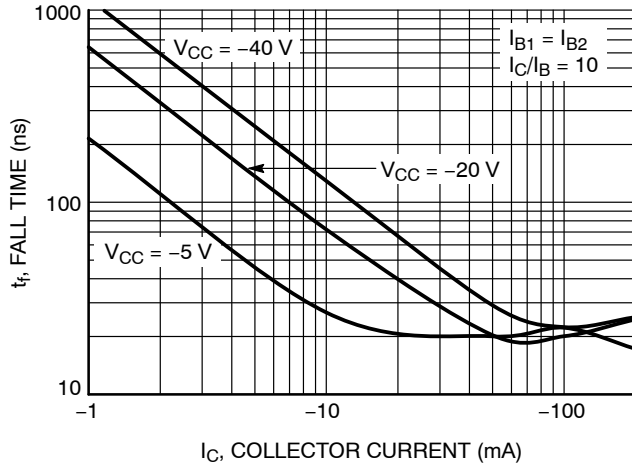


Figure 7. Fall Time

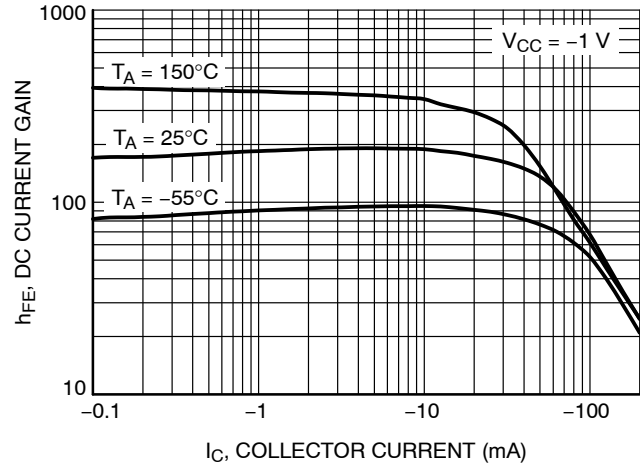


Figure 8. DC Current Gain

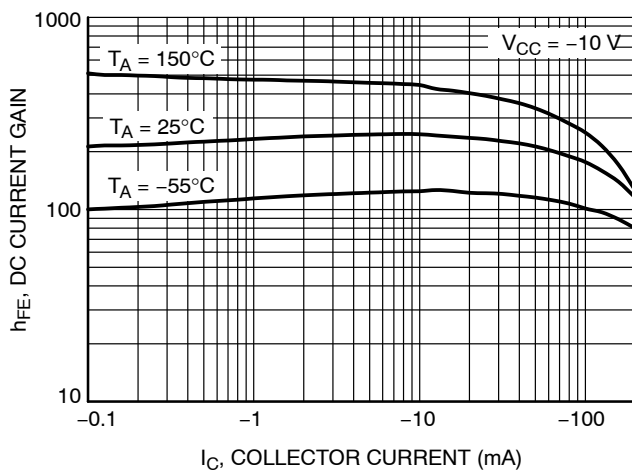


Figure 9. DC Current Gain

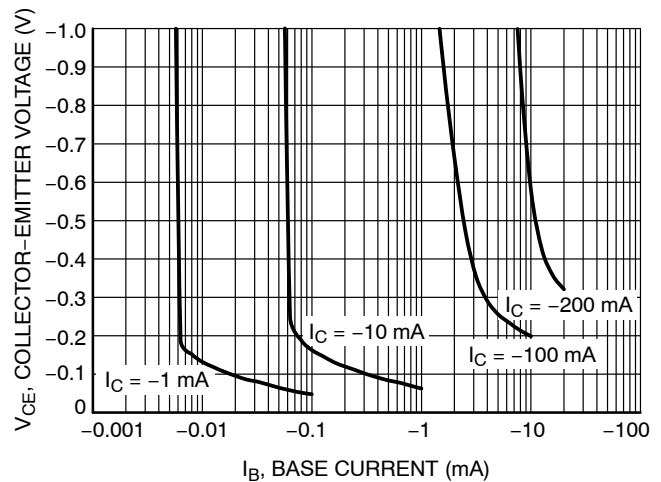


Figure 10. Collector Saturation Region

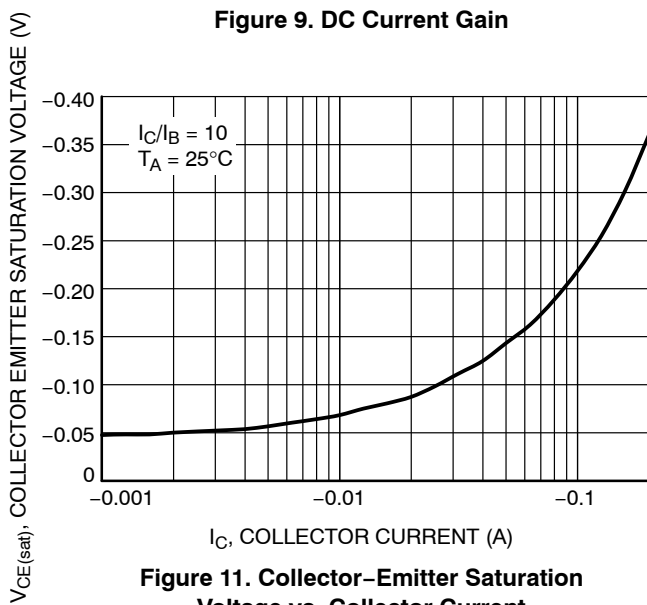


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

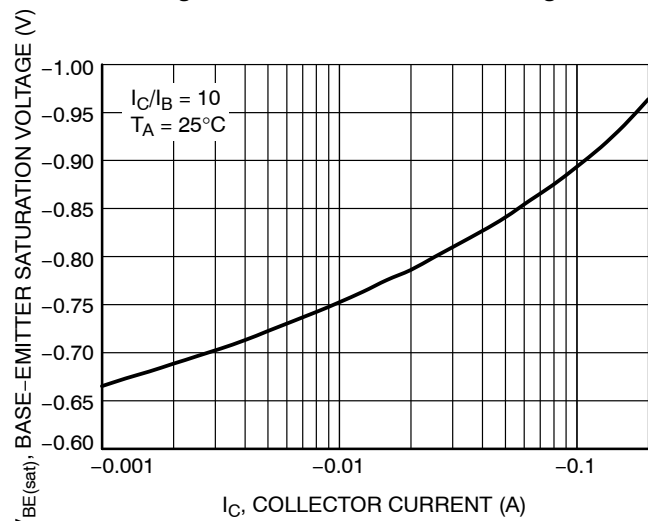


Figure 12. Base-Emitter Saturation Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

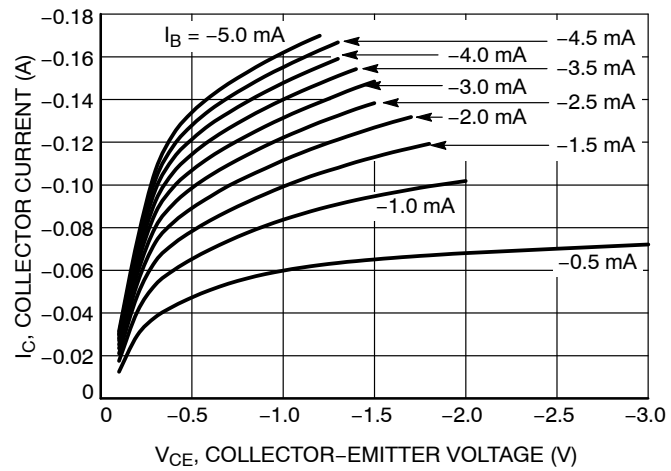


Figure 13. Collector Current vs. Collector-Emitter Voltage

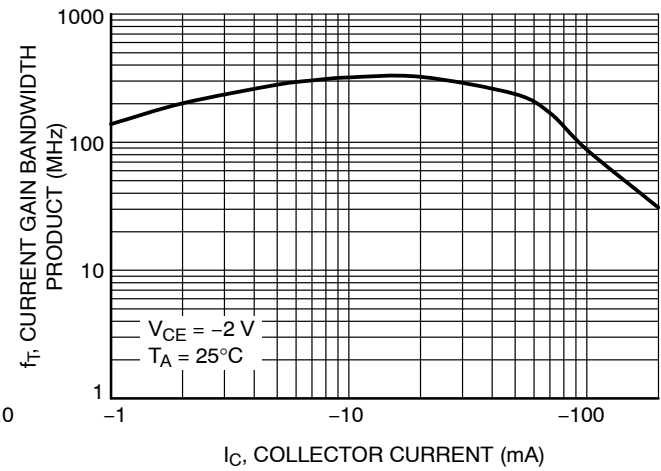


Figure 14. Current Gain Bandwidth vs. Collector Current

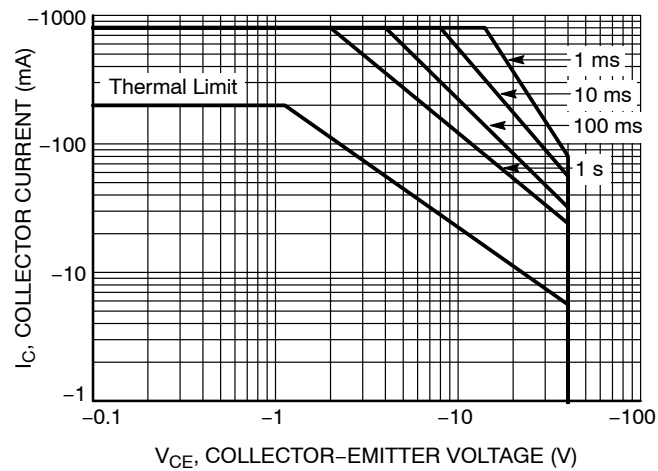
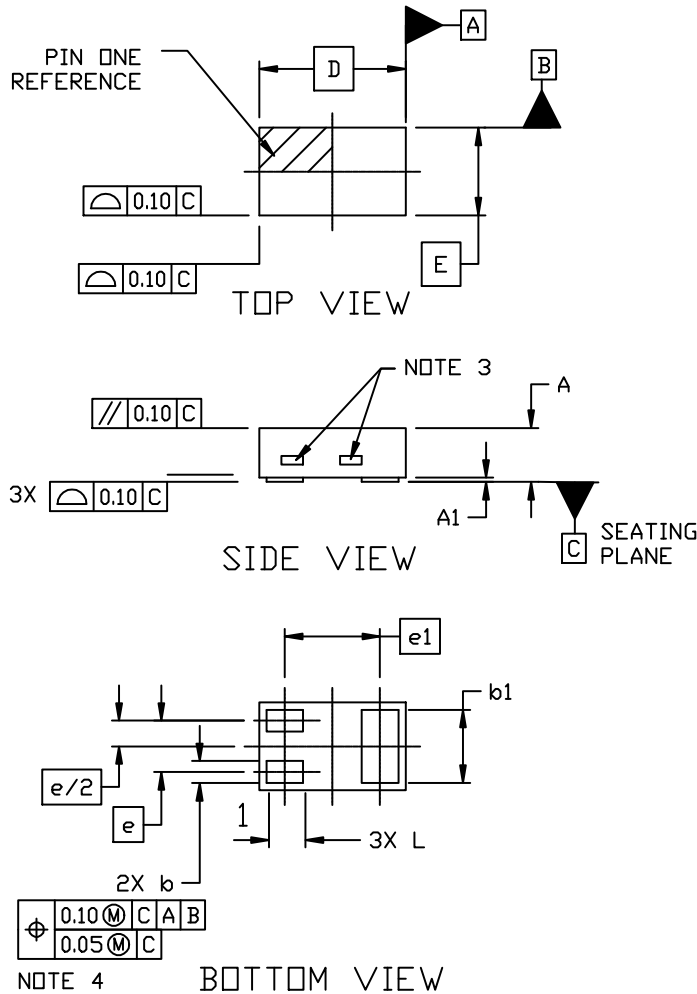


Figure 15. Safe Operating Area

NST3906MX2

PACKAGE DIMENSIONS

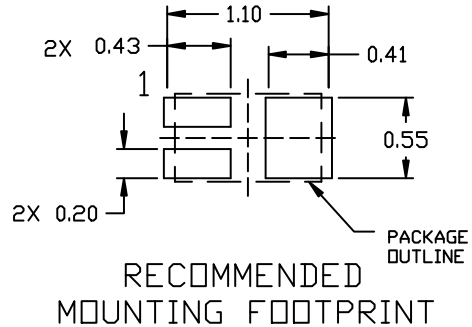
X2DFN3 1.0x0.6, 0.35P
CASE 714AC
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. EXPOSED COPPER ALLOWED AS SHOWN.
4. ALL PAD LOCATIONS CONTROLLED WITH THIS POSITIONAL TOLERANCE.

DIM	MILLIMETERS		
	MIN.	MAX.	MAX.
A	0.34	0.37	0.40
A1	0.00	---	0.05
b	0.10	0.15	0.20
b1	0.45	0.50	0.55
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	0.35 BSC		
e1	0.65 BSC		
L	0.20	0.25	0.30



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